

RF Power Field Effect Transistors

High Ruggedness N-Channel Enhancement-Mode Lateral MOSFETs

These high ruggedness devices are designed for use in high VSWR industrial (including laser and plasma exciters), broadcast (analog and digital), aerospace and radio/land mobile applications. They are unmatched input and output designs allowing wide frequency range utilization, between 1.8 and 600 MHz.

- Typical Performance: $V_{DD} = 50$ Volts, $I_{DQ} = 100$ mA

Signal Type	P_{out} (W)	f (MHz)	G_{ps} (dB)	η_D (%)	IRL (dB)
Pulsed (100 μ sec, 20% Duty Cycle)	600 Peak	230	25.0	74.6	-18
CW	600 Avg.	230	24.6	75.2	-17

- Capable of Handling a Load Mismatch of 65:1 VSWR, @ 50 Vdc, 230 MHz, at all Phase Angles, Designed for Enhanced Ruggedness
 - 600 Watts Pulsed Peak Power, 20% Duty Cycle, 100 μ sec

Features

- Unmatched Input and Output Allowing Wide Frequency Range Utilization
- Device can be used Single-Ended or in a Push-Pull Configuration
- Qualified Up to a Maximum of 50 V_{DD} Operation
- Characterized from 30 V to 50 V for Extended Power Range
- Suitable for Linear Application with Appropriate Biasing
- Integrated ESD Protection with Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- RoHS Compliant
- In Tape and Reel. R6 Suffix = 150 Units, 56 mm Tape Width, 13 inch Reel. For R5 Tape and Reel options, see p. 12.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +130	Vdc
Gate-Source Voltage	V_{GS}	-6.0, +10	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	$^{\circ}$ C
Case Operating Temperature	T_C	150	$^{\circ}$ C
Total Device Dissipation @ $T_C = 25^{\circ}$ C Derate above 25 $^{\circ}$ C	P_D	1667 8.33	W W/ $^{\circ}$ C
Operating Junction Temperature (1,2)	T_J	225	$^{\circ}$ C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case			$^{\circ}$ C/W
Case Temperature 68 $^{\circ}$ C, 600 W Pulsed, 100 μ sec Pulse Width, 20% Duty Cycle, 100 mA, 230 MHz	$Z_{\theta JC}$	0.022	
Case Temperature 60 $^{\circ}$ C, 600 W CW, 100 mA, 230 MHz	$R_{\theta JC}$	0.12	

- Continuous use at maximum temperature will affect MTTF.
- MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
- Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

MRFE6VP5600HR6 MRFE6VP5600HSR6

**1.8-600 MHz, 600 W CW, 50 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs**

**CASE 375D-05, STYLE 1
NI-1230
MRFE6VP5600HR6**

**CASE 375E-04, STYLE 1
NI-1230S
MRFE6VP5600HSR6**

PARTS ARE PUSH-PULL

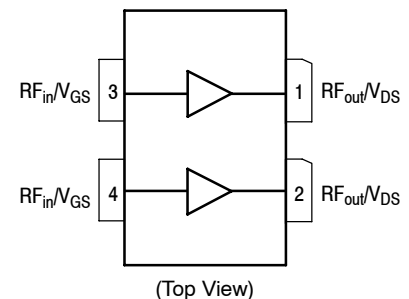


Figure 1. Pin Connections

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	B (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

Off Characteristics ⁽¹⁾

Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 100\text{ mA}$)	$V_{(BR)DSS}$	130	—	—	Vdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 50\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 100\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	20	μAdc

On Characteristics

Gate Threshold Voltage ⁽¹⁾ ($V_{DS} = 10\text{ Vdc}$, $I_D = 960\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	1.7	2.2	2.7	Vdc
Gate Quiescent Voltage ($V_{DD} = 50\text{ Vdc}$, $I_D = 100\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	2.0	2.5	3.0	Vdc
Drain-Source On-Voltage ⁽¹⁾ ($V_{GS} = 10\text{ Vdc}$, $I_D = 2\text{ Adc}$)	$V_{DS(on)}$	—	0.26	—	Vdc

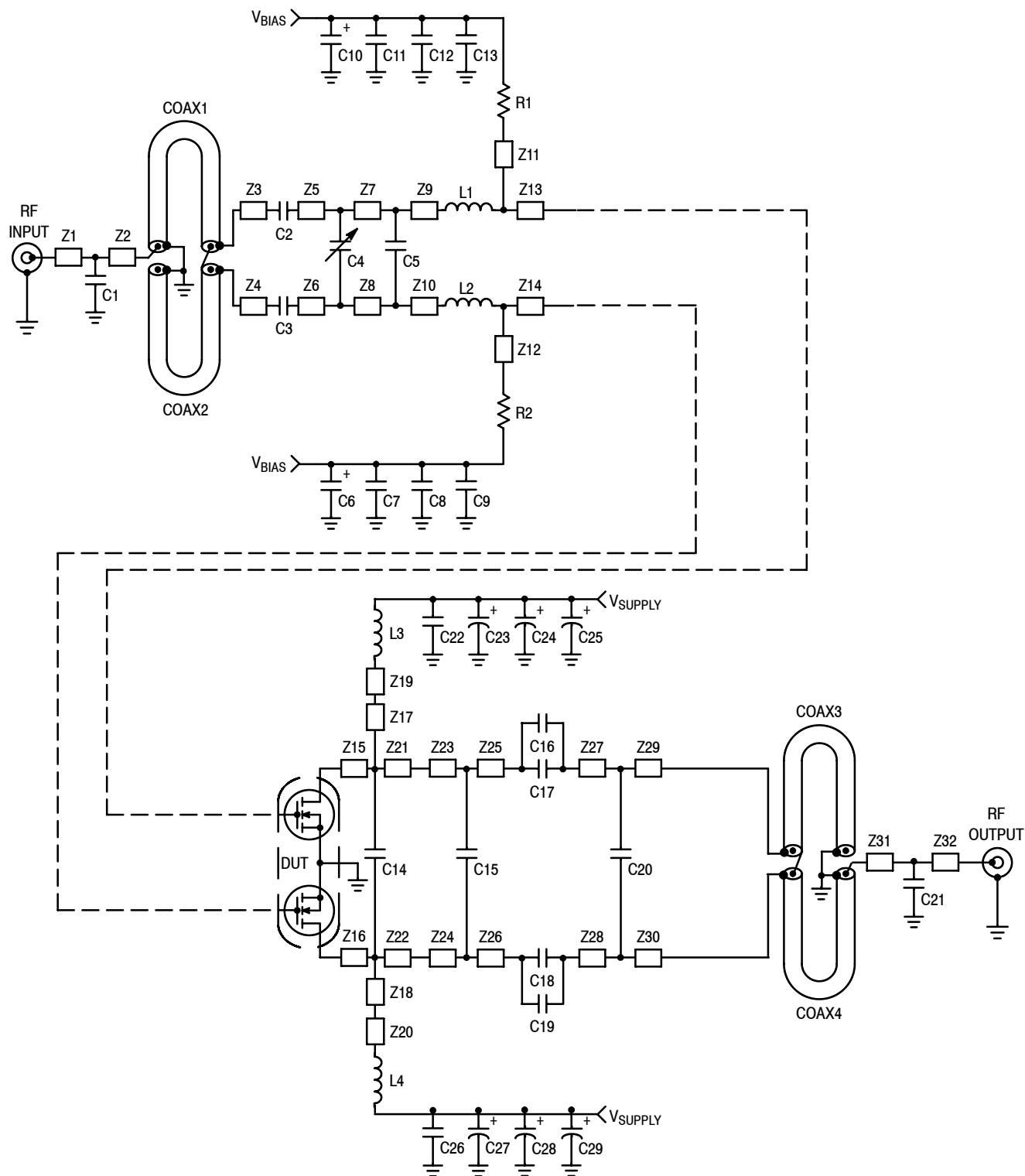
Dynamic Characteristics ⁽¹⁾

Reverse Transfer Capacitance ($V_{DS} = 50\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	1.60	—	pF
Output Capacitance ($V_{DS} = 50\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	129	—	pF
Input Capacitance ($V_{DS} = 50\text{ Vdc}$, $V_{GS} = 0\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz)	C_{iss}	—	342	—	pF

Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 50\text{ Vdc}$, $I_{DQ} = 100\text{ mA}$, $P_{out} = 600\text{ W Peak}$ (120 W Avg.), $f = 230\text{ MHz}$, Pulsed, 100 μsec Pulse Width, 20% Duty Cycle

Power Gain	G_{ps}	23.5	25.0	26.5	dB
Drain Efficiency	η_D	73.5	74.6	—	%
Input Return Loss	IRL	—	-18	-12	dB

1. Each side of device measured separately.



Z1	0.192" x 0.082" Microstrip
Z2	0.175" x 0.082" Microstrip
Z3, Z4	0.170" x 0.100" Microstrip
Z5, Z6	0.116" x 0.285" Microstrip
Z7, Z8	0.116" x 0.285" Microstrip
Z9, Z10	0.108" x 0.285" Microstrip

Z11*, Z12*	0.872" x 0.058" Microstrip
Z13, Z14	0.412" x 0.726" Microstrip
Z15, Z16	0.371" x 0.507" Microstrip
Z17*, Z18*	0.466" x 0.363" Microstrip
Z19*, Z20*	1.187" x 0.154" Microstrip
Z21, Z22	0.104" x 0.507" Microstrip

Z23, Z24	1.251" x 0.300" Microstrip
Z25, Z26	0.127" x 0.300" Microstrip
Z27, Z28	0.058" x 0.300" Microstrip
Z29, Z30	0.058" x 0.300" Microstrip
Z31	0.186" x 0.082" Microstrip
Z32	0.179" x 0.082" Microstrip

* Line length includes microstrip bends

Figure 1. MRFE6VP5600HR6(HSR6) Test Circuit Schematic - Pulsed

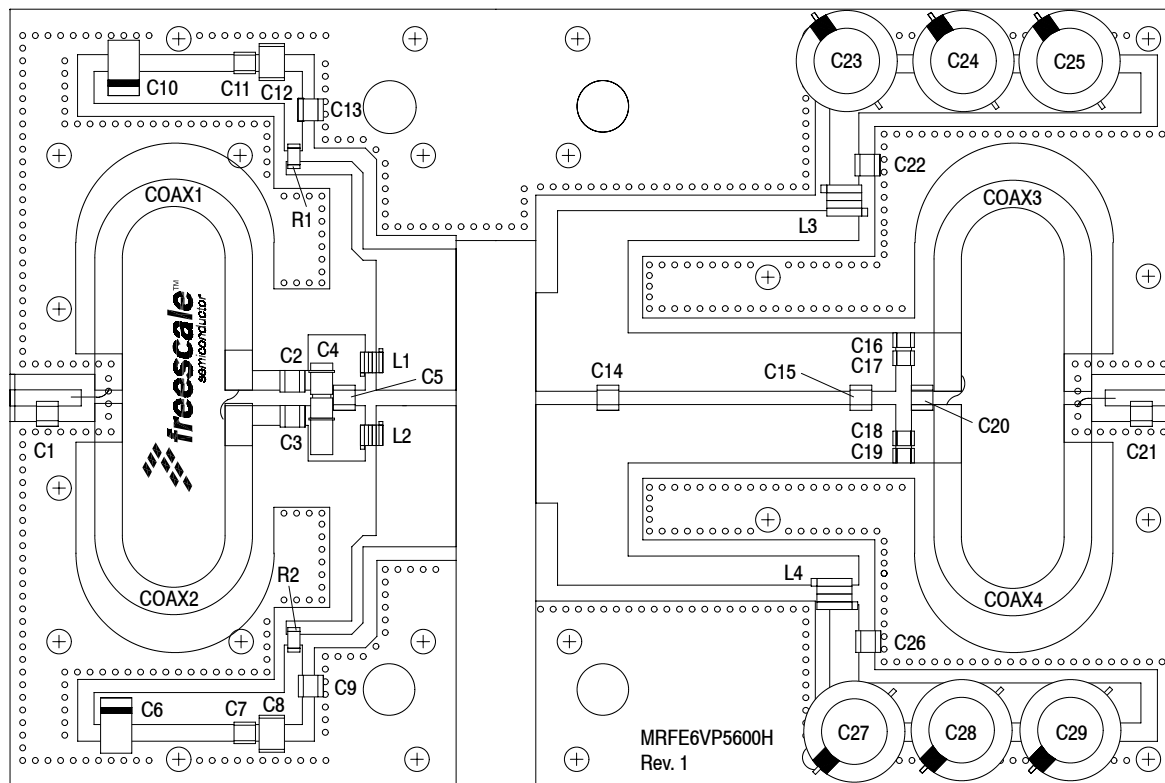
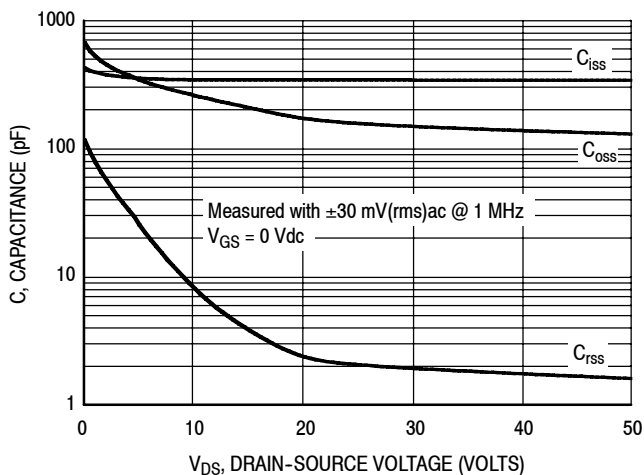


Figure 2. MRFE6VP5600HR6(HSR6) Test Circuit Component Layout - Pulsed

Table 5. MRFE6VP5600HR6(HSR6) Test Circuit Component Designations and Values - Pulsed

Part	Description	Part Number	Manufacturer
C1	12 pF Chip Capacitor	ATC100B120JT500XT	ATC
C2, C3	27 pF Chip Capacitors	ATC100B270JT500XT	ATC
C4	0.8–8.0 pF Variable Capacitor, Gigatrim	27291SL	Johanson
C5	33 pF Chip Capacitor	ATC100B330JT500XT	ATC
C6, C10	22 μ F, 35 V Tantalum Capacitors	T491X226K035AT	Kemet
C7, C11	0.1 μ F Chip Capacitors	CDR33BX104AKYS	AVX
C8, C12	220 nF Chip Capacitors	C1812C224K5RACTU	Kemet
C9, C13, C22, C26	1000 pF Chip Capacitors	ATC100B102JT50XT	ATC
C14	36 pF Chip Capacitor	ATC100B360JT500XT	ATC
C15	51 pF Chip Capacitor	ATC100B510GT500XT	ATC
C16, C17, C18, C19	240 pF Chip Capacitors	ATC100B241JT200XT	ATC
C20	39 pF Chip Capacitor	ATC100B390JT500XT	ATC
C21	10 pF Chip Capacitor	ATC100B100JT500XT	ATC
C23, C24, C25, C27, C28, C29	470 μ F, 63 V Electrolytic Capacitors	MCGPR63V477M13X26–RH	Multicomp
Coax1, 2, 3, 4	25 Ω Semi Rigid Coax, 2.2" Long	UT-141C-25	Micro Coax
L1, L2	5 nH Inductors	A02TKLC	Coilcraft
L3, L4	6.6 nH Inductors	GA3093-ALC	Coilcraft
R1, R2	10 Ω Chip Resistors	CRCW120610R0JNEA	Vishay
PCB	0.030", $\epsilon_r = 2.55$	AD255A	Arlon

TYPICAL CHARACTERISTICS



Note: Each side of device measured separately.

Figure 3. Capacitance versus Drain-Source Voltage

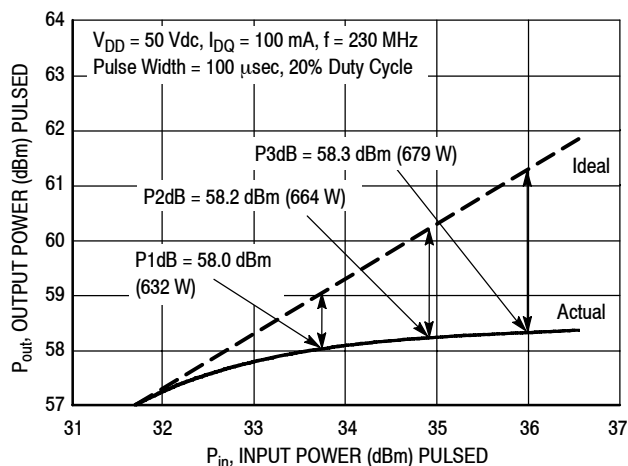


Figure 4. Pulsed Output Power versus Input Power

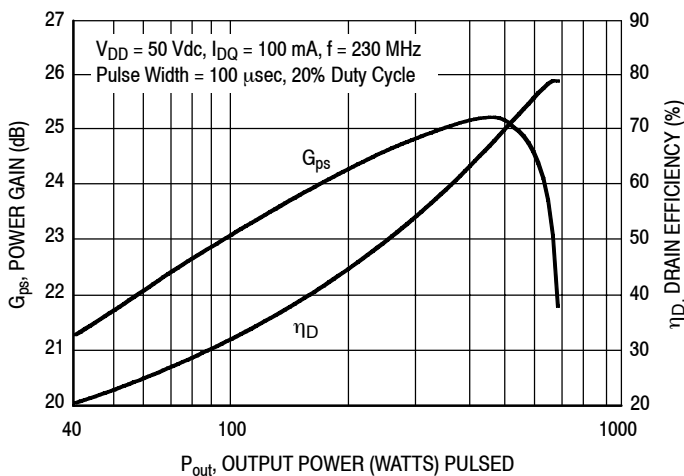


Figure 5. Pulsed Power Gain and Drain Efficiency versus Output Power

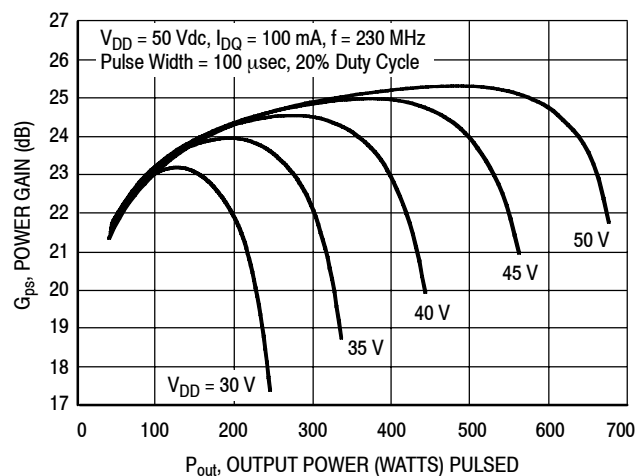


Figure 6. Pulsed Power Gain versus Output Power

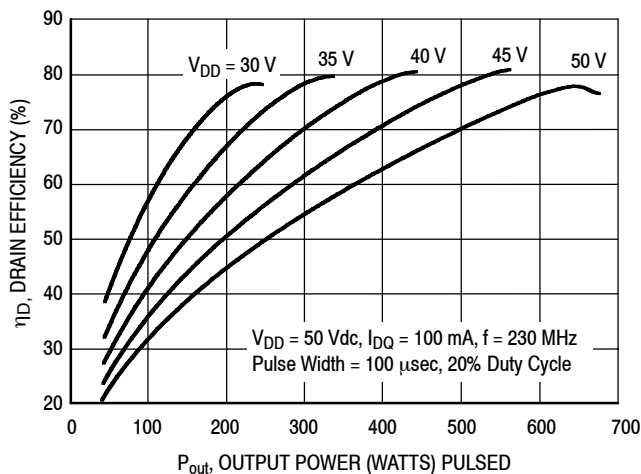


Figure 7. Pulsed Drain Efficiency versus Output Power

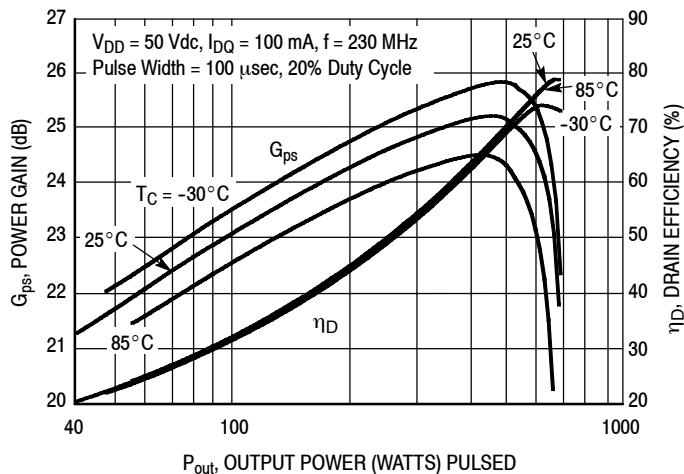
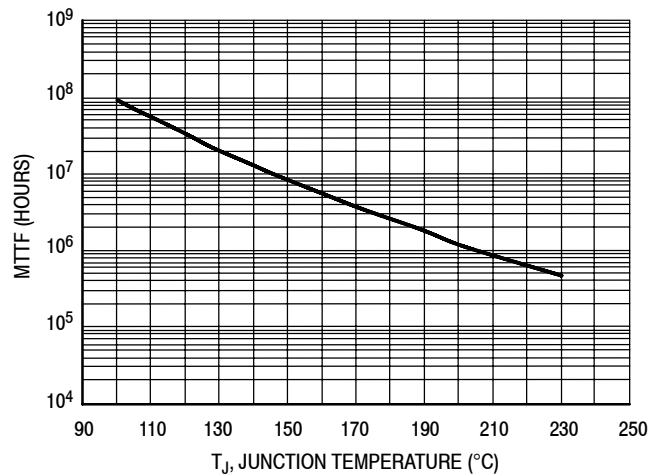


Figure 8. Pulsed Power Gain and Drain Efficiency versus Output Power

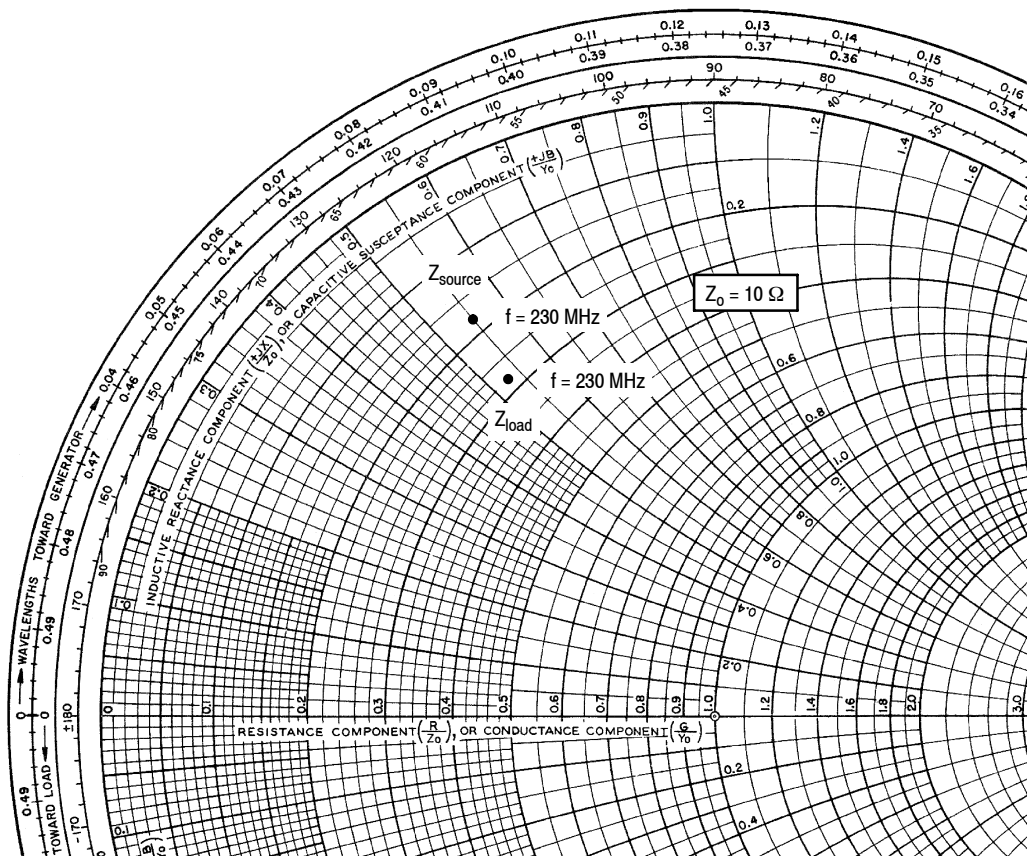
TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 50$ Vdc, $P_{out} = 600$ W Avg., and $\eta_D = 75.2\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 9. MTTF versus Junction Temperature — CW



$V_{DD} = 50 \text{ Vdc}$, $I_{DQ} = 100 \text{ mA}$, $P_{out} = 600 \text{ W Peak}$

f MHz	Z_{source} Ω	Z_{load} Ω
230	$1.78 + j5.45$	$2.75 + j5.30$

Z_{source} = Test circuit impedance as measured from gate to gate, balanced configuration.

Z_{load} = Test circuit impedance as measured from drain to drain, balanced configuration.

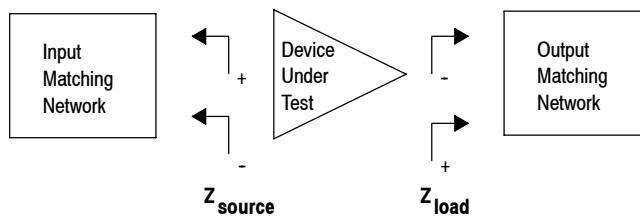
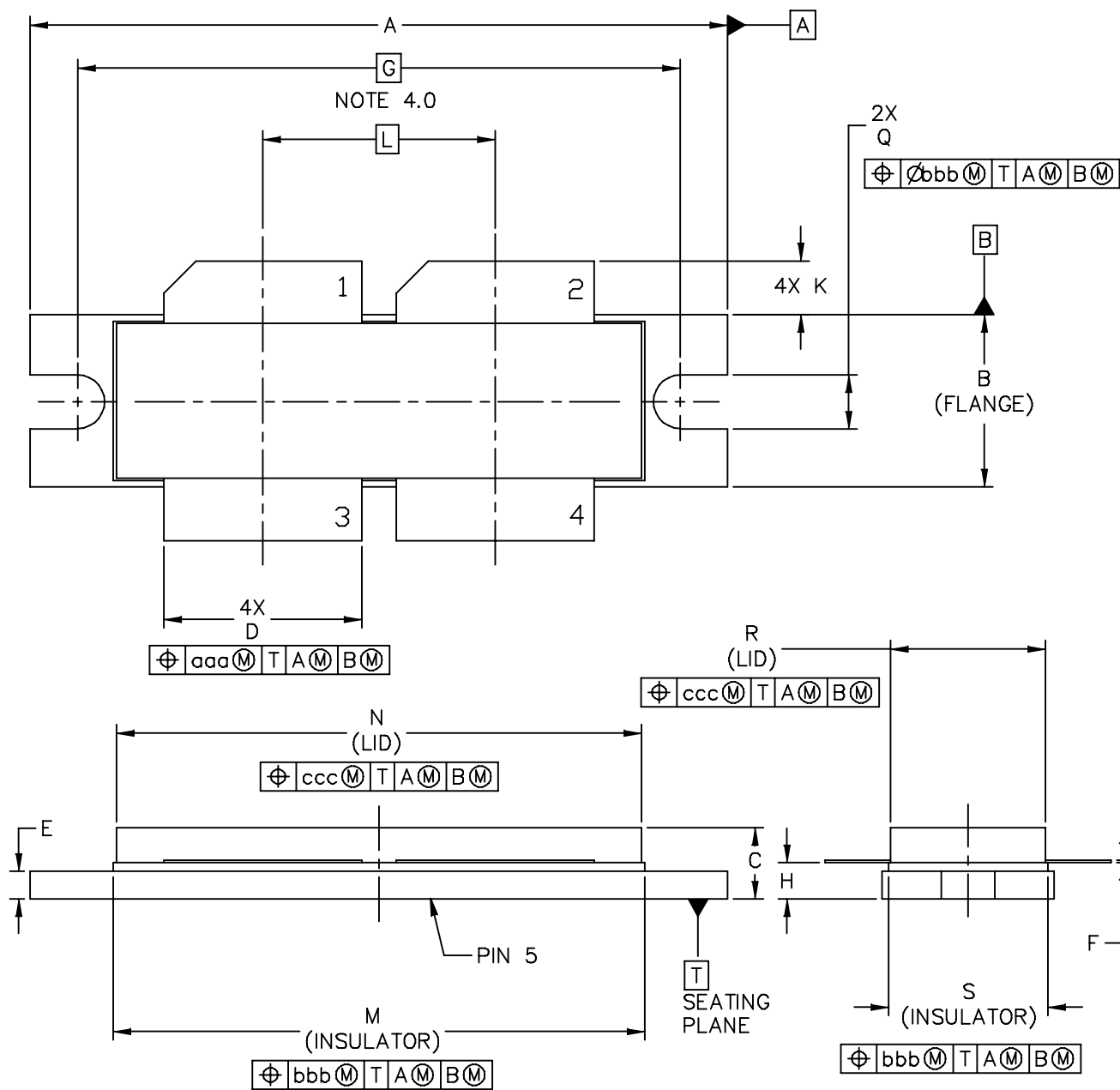


Figure 10. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.		MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE
TITLE: NI-1230	DOCUMENT NO: 98ASB16977C		REV: E
	CASE NUMBER: 375D-05		31 MAR 2005
	STANDARD: NON-JEDEC		

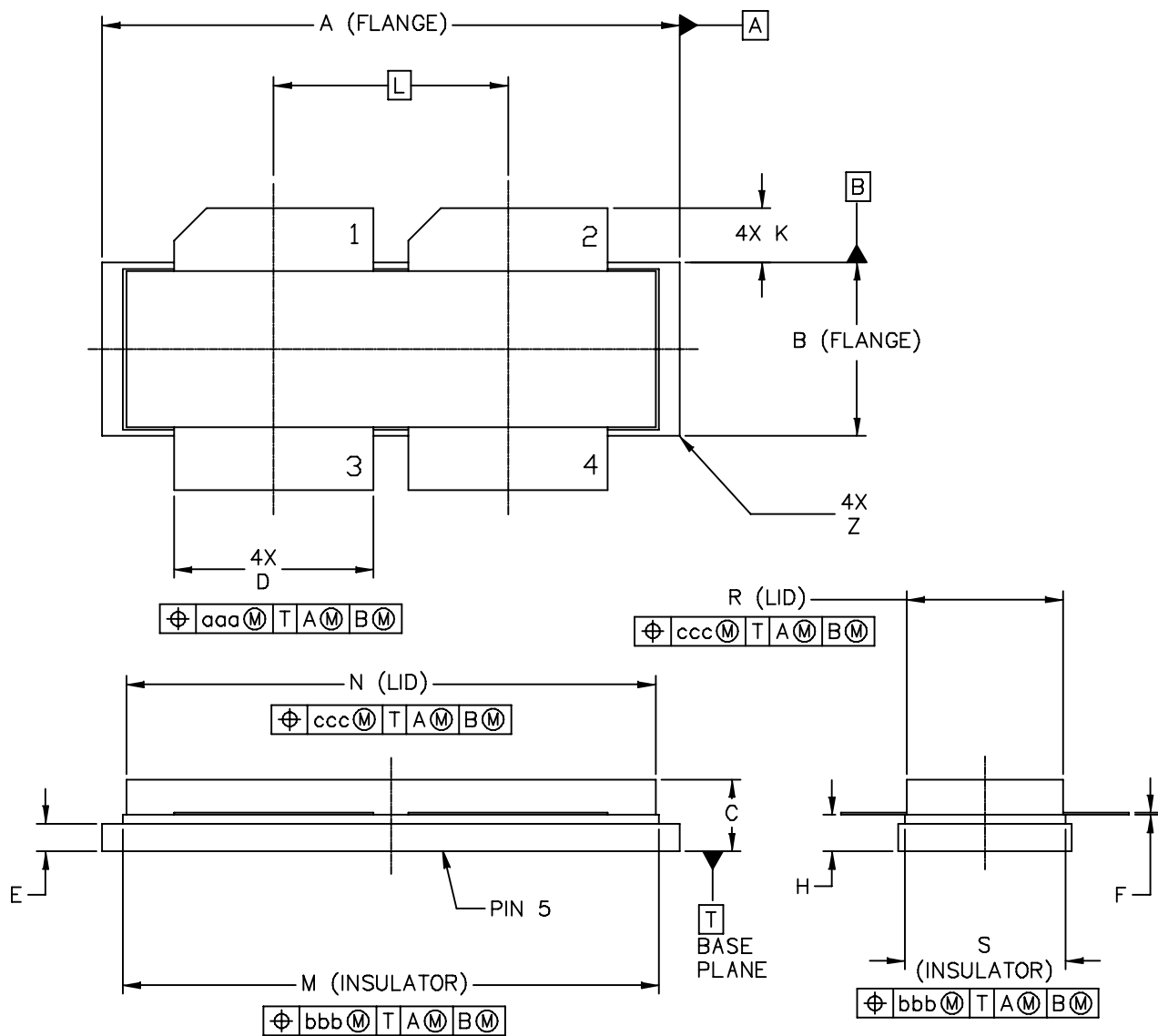
NOTES:

- 1.0 INTERPRET DIMENSIONS AND TOLERANCES
PER ASME Y14.5M-1994.
- 2.0 CONTROLLING DIMENSION: INCH
- 3.0 DIMENSION H IS MEASURED .030 (0.762)
AWAY FROM PACKAGE BODY.
- 4.0 RECOMMENDED BOLT CENTER DIMENSION OF
1.52 (38.61) BASED ON M3 SCREW.

STYLE 1:

- PIN 1 – DRAIN
 2 – DRAIN
 3 – GATE
 4 – GATE
 5 – SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.615	1.625	41.02	41.28	N	1.218	1.242	30.94	31.55
B	.395	.405	10.03	10.29	Q	.120	.130	3.05	3.3
C	.150	.200	3.81	5.08	R	.355	.365	9.01	9.27
D	.455	.465	11.56	11.81	S	.365	.375	9.27	9.53
E	.062	.066	1.57	1.68					
F	.004	.007	0.1	0.18					
G	1.400 BSC		35.56 BSC		aaa	.013		0.33	
H	.082	.090	2.08	2.29	bbb	.010		0.25	
K	.117	.137	2.97	3.48	ccc	.020		0.51	
L	.540 BSC		13.72 BSC						
M	1.219	1.241	30.96	31.52					
© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.				MECHANICAL OUTLINE		PRINT VERSION NOT TO SCALE			
TITLE: NI-1230					DOCUMENT NO: 98ASB16977C				REV: E
					CASE NUMBER: 375D-05				31 MAR 2005
					STANDARD: NON-JEDEC				



© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.		MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE
TITLE: NI-1230S		DOCUMENT NO: 98ARB18247C	REV: F
		CASE NUMBER: 375E-04	05 AUG 2005
		STANDARD: NON-JEDEC	

NOTES:

1. INTERPRET DIMENSIONS AND TOLERANCES
PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH
3. DIMENSION H IS MEASURED .030
AWAY FROM PACKAGE BODY

STYLE 1:

- PIN 1 - DRAIN
2 - DRAIN
3 - GATE
4 - GATE
5 - SOURCE

DIM	INCHES		MILLIMETERS		DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.265	1.275	32.13	32.38	R	.355	.365	9.01	9.27
B	.395	.405	10.03	10.29	S	.365	.375	9.27	9.53
C	.150	.200	3.81	5.08	Z	---	.040	---	1.02
D	.455	.465	11.56	11.81					
E	.062	.066	1.57	1.68	aaa	.013		0.33	
F	.004	.007	0.1	0.18	bbb	.010		0.25	
H	.082	.090	2.08	2.29	ccc	.020		0.51	
K	.117	.137	2.97	3.48					
L	.540 BSC		13.72 BSC						
M	1.219	1.241	30.96	31.52					
N	1.218	1.242	30.94	31.55					
© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.			MECHANICAL OUTLINE			PRINT VERSION NOT TO SCALE			
TITLE: NI-1230S					DOCUMENT NO: 98ARB18247C				REV: F
					CASE NUMBER: 375E-04				05 AUG 2005
					STANDARD: NON-JEDEC				

PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following documents and software to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator
- RF High Power Model
- .s2p File

For Software, do a Part Number search at <http://www.freescale.com>, and select the "Part Number" link. Go to the Software & Tools tab on the part's Product Summary page to download the respective tool.

R5 TAPE AND REEL OPTION

R5 Suffix = 50 Units, 56 mm Tape Width, 13 inch Reel.

The R5 tape and reel option for MRFE6VP5600H and MRFE6VP5600HS parts will be available for 2 years after release of MRFE6VP5600H and MRFE6VP5600HS. Freescale Semiconductor, Inc. reserves the right to limit the quantities that will be delivered in the R5 tape and reel option. At the end of the 2 year period customers who have purchased these devices in the R5 tape and reel option will be offered MRFE6VP5600H and MRFE6VP5600HS in the R6 tape and reel option.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Dec. 2010	• Initial Release of Data Sheet
1	Jan. 2011	• Fig. 1, Pin Connections, corrected pin 4 label from RF_{out}/V_{GS} to RF_{in}/V_{GS} , p. 1

How to Reach Us:

Home Page:

www.freescale.com

Web Support:

<http://www.freescale.com/support>

USA/Europe or Locations Not Listed:

Freescale Semiconductor, Inc.
Technical Information Center, EL516
2100 East Elliot Road
Tempe, Arizona 85284
1-800-521-6274 or +1-480-768-2130
www.freescale.com/support

Europe, Middle East, and Africa:

Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
+44 1296 380 456 (English)
+46 8 52200080 (English)
+49 89 92103 559 (German)
+33 1 69 35 48 48 (French)
www.freescale.com/support

Japan:

Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:

Freescale Semiconductor China Ltd.
Exchange Building 23F
No. 118 Jianguo Road
Chaoyang District
Beijing 100022
China
+86 10 5879 8000
support.asia@freescale.com

For Literature Requests Only:

Freescale Semiconductor Literature Distribution Center
1-800-441-2447 or +1-303-675-2140
Fax: +1-303-675-2150
LDCForFreescaleSemiconductor@hibbertgroup.com

Information in this document is provided solely to enable system and software implementers to use Freescale Semiconductor products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits or integrated circuits based on the information in this document.

Freescale Semiconductor reserves the right to make changes without further notice to any products herein. Freescale Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Freescale Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters that may be provided in Freescale Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals", must be validated for each customer application by customer's technical experts. Freescale Semiconductor does not convey any license under its patent rights nor the rights of others. Freescale Semiconductor products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Freescale Semiconductor product could create a situation where personal injury or death may occur. Should Buyer purchase or use Freescale Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold Freescale Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Freescale Semiconductor was negligent regarding the design or manufacture of the part.

Freescale™ and the Freescale logo are trademarks of Freescale Semiconductor, Inc. All other product or service names are the property of their respective owners.

© Freescale Semiconductor, Inc. 2010-2011. All rights reserved.